

PATENT ABSTRACTS OF JAPAN

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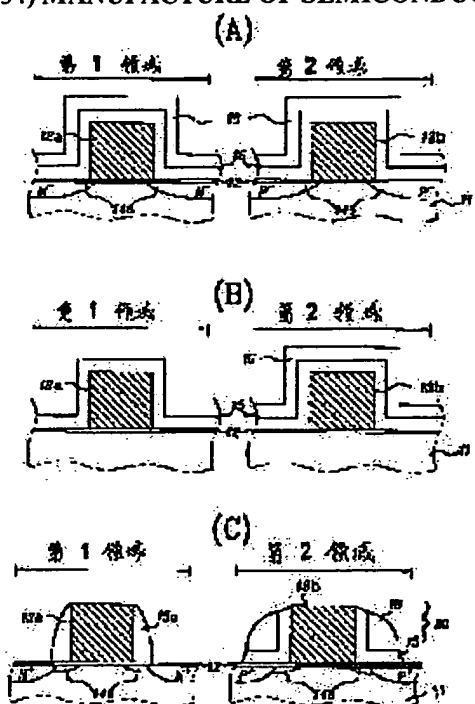
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(54) MANUFACTURE OF SEMICONDUCTOR DEVICE



(57)Abstract:

PROBLEM TO BE SOLVED: To increase device driving current by improving short channel characteristics.

SOLUTION: A first insulating film 15 and a second insulating film 16 having excellent selectivity in wet etching are formed on polysilicon gates 13a and 13b respectively formed in a first and a second regions. Then, the second insulating film 16 is coated with a photosensitive film. The photosensitive film is removed at portions where side wall spaces 15a and 20 are to be formed, and anisotropic etching is performed on the photosensitive film, so as to selectively form the side wall spaces 15a and 20. At this time, the side wall space 20 is formed from the first and second insulating films 15 and 16 such that the thickness of the side wall space 20 is greater than that of the side wall space 15a. This improves short channel characteristics